Application No.: 09/588,

Docke o.: M4065.0210/P210

98. (new) A capacitor for a semiconductor device, said capacitor comprising:

a bottom conducting layer;

a dielectric layer over said bottom conducting layer; and

an annealed top conducting layer over said dielectric layer, wherein each of said bottom and annealed top conducting layers is formed of a material selected from the group consisting of platinum, platinum rhodium, platinum iridium, and tungsten nitride.